

Development of a new generation of 3D pixel sensors for HL-LHC

G.-F. Dalla Betta^{a,b,*}, M. Boscardin^{c,b}, G. Darbo^d, R. Mendicino^{a,b}, M. Meschini^c, A. Messineo^{f,g}, S. Ronchin^c,
D M S Sultan^{a,b}, N. Zorzi^{c,b}

^a *Università di Trento, Dipartimento di Ingegneria Industriale, I-38123 Trento, Italy*

^b *TIFPA INFN, I-38123 Trento, Italy*

^c *Fondazione Bruno Kessler, I-38123 Trento, Italy*

^d *INFN Sezione di Genova, I-16146 Genova, Italy*

^e *INFN Sezione di Firenze, I-50019 Sesto Fiorentino, Italy*

^f *Università di Pisa, Dipartimento di Fisica, I-56127 Pisa, Italy*

^g *INFN, Sezione di Pisa, I-56127 Pisa, Italy*

Abstract

This paper covers the main technological and design aspects relevant to the development of a new generation of thin 3D pixel sensors with small pixel size aimed at the High-Luminosity LHC upgrades.

Keywords: 3D silicon sensors; Deep Reactive Ion Etching; Fabrication technology.

1. Introduction

After their successful application to the ATLAS Insertable B-Layer (IBL) [1], and owing to their intrinsic radiation hardness, 3D pixel sensors are considered a viable option for the “Phase 2” upgrades at the High-Luminosity LHC (HL-LHC), in particular for the innermost tracking layers of ATLAS and CMS, which will have to cope with extreme radiation fluences (up to 2×10^{16} n_{eq} cm⁻²). To this purpose, we are developing a new generation of 3D pixels optimized for increased pixel granularity (25×100 or 50×50 μm² pixel size), reduced material budget and better geometrical efficiency. Compared to the double-sided 3D sensors produced at FBK for the ATLAS IBL [2], these requirements call for a modified (single-sided) technology allowing for downscaled sensor dimensions: thinner active layers (~100 μm), narrower electrodes (~5 μm), reduced inter-electrode spacing (~30 μm), and very slim (~100 μm) or active edges.

2. Process development

Due to mechanical yield issues, we propose a new 3D structure made with a single-sided approach on Silicon-Silicon Direct Wafer Bonded (SiSi DWB) substrates from IceMOS Technology Ltd. (Belfast, UK), consisting of a p⁻ Float Zone High-Resistivity (HR) layer of the desired thickness (e.g., 100 or 130 μm for sensors of the first batch) directly bonded to a p⁺⁺ Low-Resistivity (LR) handle wafer (see Fig. 1a).

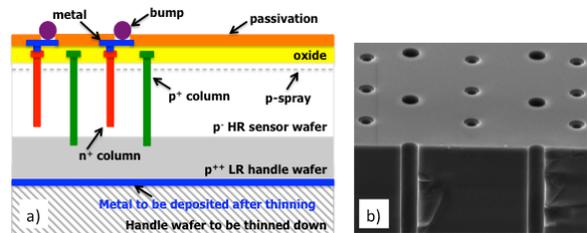


Figure 1 (a) Schematic cross-section of the proposed thin 3D sensors on SiSi DWB substrate, and (b) SEM micrograph of two sets of columns etched by DRIE (misalignment is intentional).

* Corresponding author. Tel.: +39-0461-283904; fax: +39-0461-281977; e-mail: gianfranco.dallabetta@unitn.it.

Besides providing a high mechanical stability, the LR handle wafer also allows the sensor bias to be applied from the back side, thus easing the front side layout. In fact, the p^+ columns are etched through the HR layer and penetrate the LR wafer, thus making a good ohmic contact that can be further improved by thinning the handle wafer and depositing a metal layer. The latter steps can be performed as a post-processing combined to the bump bonding process.

The n^+ (read-out) columns, isolated at the surface by a p-spray layer, are not etched completely through the HR layer, but they rather stop at a short distance ($\sim 15 \mu\text{m}$) from the handle wafer in order to ensure a high breakdown voltage (higher than 100 V before irradiation), as already proved in existing devices [3] and confirmed by TCAD simulations for new ones.

Both types of columns are etched from the same wafer side (that was not the case for the previous double-sided process [3]). This modified approach was successfully proved at FBK (see Fig. 1b): a first set of narrow columns was etched by Deep Reactive Ion Etching (DRIE), followed by column partial filling with poly-Si. Then, a second set of wider columns was etched by DRIE without any problem.

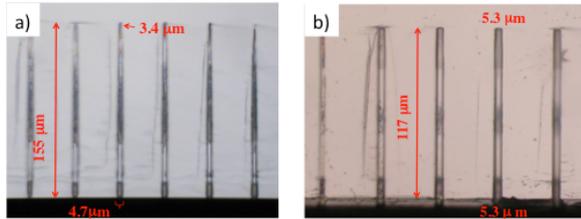


Figure 2 SEM micrographs of (a) ohmic columns, and (b) junction columns etched by DRIE.

The different depths of the two types of columns require different etching recipes. As an example, Fig. 2 shows the SEM micrograph of ohmic and junction columns aimed at the $130 \mu\text{m}$ HR layer thickness. The etching of ohmic columns (Fig. 2a) was optimized for depth in order to reach the LR handle wafer. This comes at the expense of a non-uniform column width that, however, is not critical for ohmic columns. On the contrary, width uniformity is essential for read-out columns to obtain a uniform electric field distribution. As can be seen from Fig. 2b, the final result is remarkably good. Similar tests with shorter columns were successfully performed also for the $100 \mu\text{m}$ HR layer thickness.

As for the pixel design, two different sizes are considered (see Fig. 3): $50 \times 50 \mu\text{m}^2$ with one n^+ column, and $25 \times 100 \mu\text{m}^2$, with two n^+ columns. The corresponding inter-electrode spacings (L) are ~ 35

μm and $\sim 28 \mu\text{m}$, respectively, making the $25 \times 100 \mu\text{m}^2$ pixel more radiation tolerant (a signal efficiency higher than 50% after $2 \times 10^{16} \text{ n}_{\text{eq}} \text{ cm}^{-2}$ has been estimated by TCAD simulations and by projections based on existing data [4]). However, the $25 \times 100 \mu\text{m}^2$ pixel, due to the presence of two read-out columns, exhibits a larger capacitance ($\sim 100 \text{ fF}$, to be compared to $\sim 50 \text{ fF}$ for the $50 \times 50 \mu\text{m}^2$ pixel) with impact on the noise. Moreover this layout is more critical, since the bump-bonding pad must be placed very near to both n^+ and p^+ columns (Fig. 3b). Alternative designs, featuring bonding pads on top of the columns, will also be tested in collaboration with bump bonding facilities (Selex and IZM).

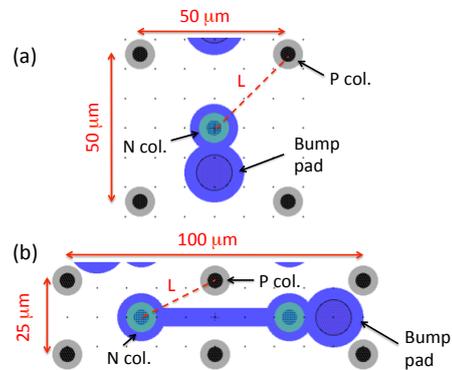


Figure 3 Layouts of (a) $50 \times 50 \mu\text{m}^2$ and (b) $25 \times 100 \mu\text{m}^2$ 3D pixels.

3. Conclusion

We have reported on the key process steps enabling the development of a new generation of 3D pixel sensors with small pixel size and thin active layers. Fabrication of a first batch of these detectors is under way at FBK.

Acknowledgment

This work was supported by the Italian National Institute for Nuclear Physics (INFN), Projects ATLAS, CMS, RD-FASE2 (CSN1), and by AIDA-2020 project EU-INFRA proposal no. 654168.

References

- [1] C. Da Via et al., Nuclear Instruments and Methods in Physics Research Section A 694 (2012) 321.
- [2] G. Giacomini et al., IEEE Transactions on Nuclear Science NS-60 (3) (2013) 2357.
- [3] G.-F. Dalla Betta et al., 2013 IEEE NSS-MIC, paper N41-1.
- [4] G.-F. Dalla Betta, PoS(IFD2014)013.